

1.021, 3.021, 10.333, 22.00 : Introduction to Modeling and Simulation : Spring 2012

Part II – Quantum Mechanical Methods : Lecture 11

A Bit More Solar PV, Some V&V and a Few Concluding Thoughts

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Part II Topics

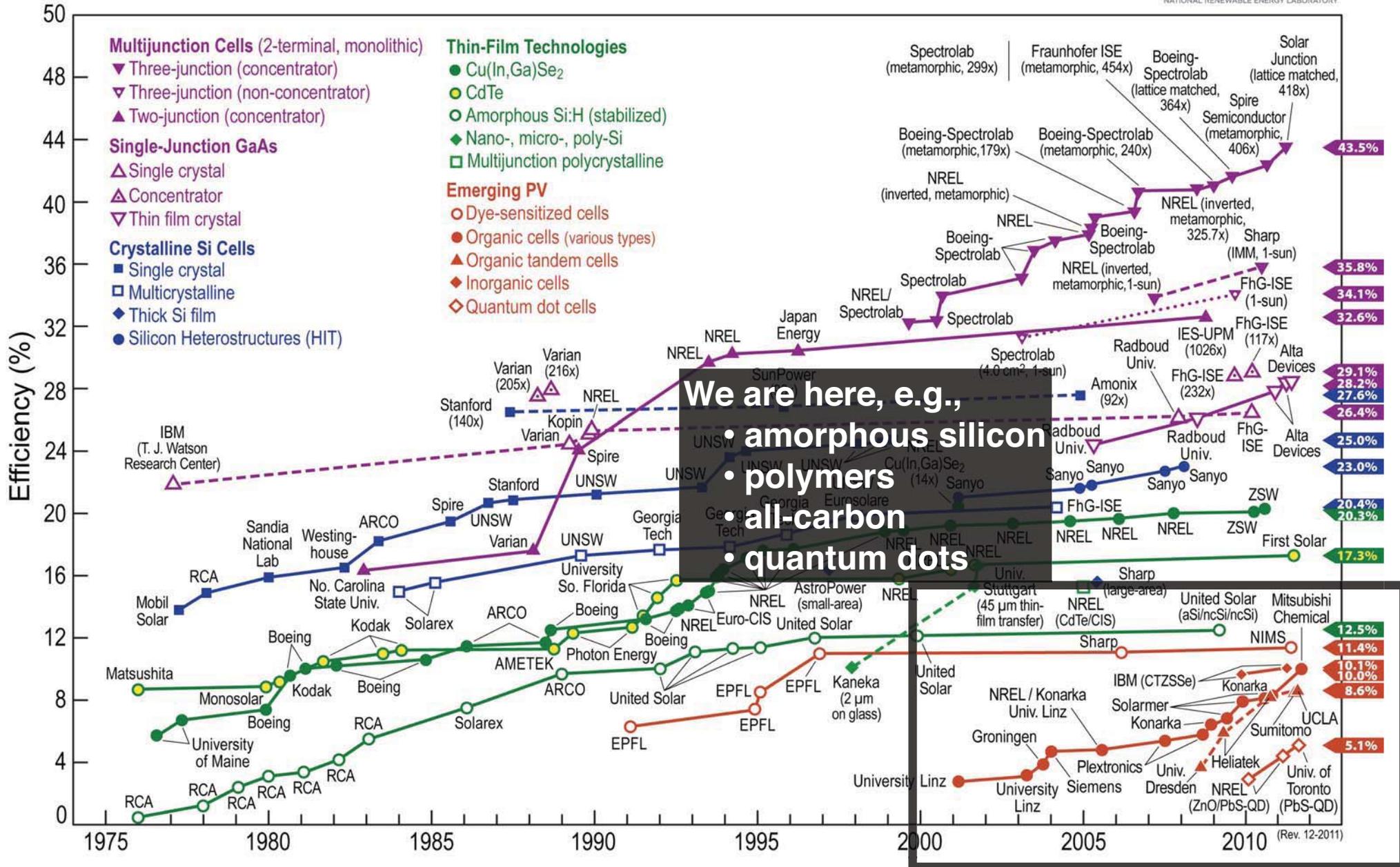
1. It's a Quantum World: The Theory of Quantum Mechanics
2. Quantum Mechanics: Practice Makes Perfect
3. From Many-Body to Single-Particle; Quantum Modeling of Molecules
4. Application of Quantum Modeling of Molecules: Solar Thermal Fuels
5. Application of Quantum Modeling of Molecules: Hydrogen Storage
6. From Atoms to Solids
7. Quantum Modeling of Solids: Basic Properties
8. Advanced Prop. of Materials: What else can we do?
9. Application of Quantum Modeling of Solids: Solar Cells Part I
10. Application of Quantum Modeling of Solids: Solar Cells Part II
11. Some PV, Some V&V and Some Concluding Thoughts

Outline

- Some more PV
- Verification and Validation
- A few more thoughts

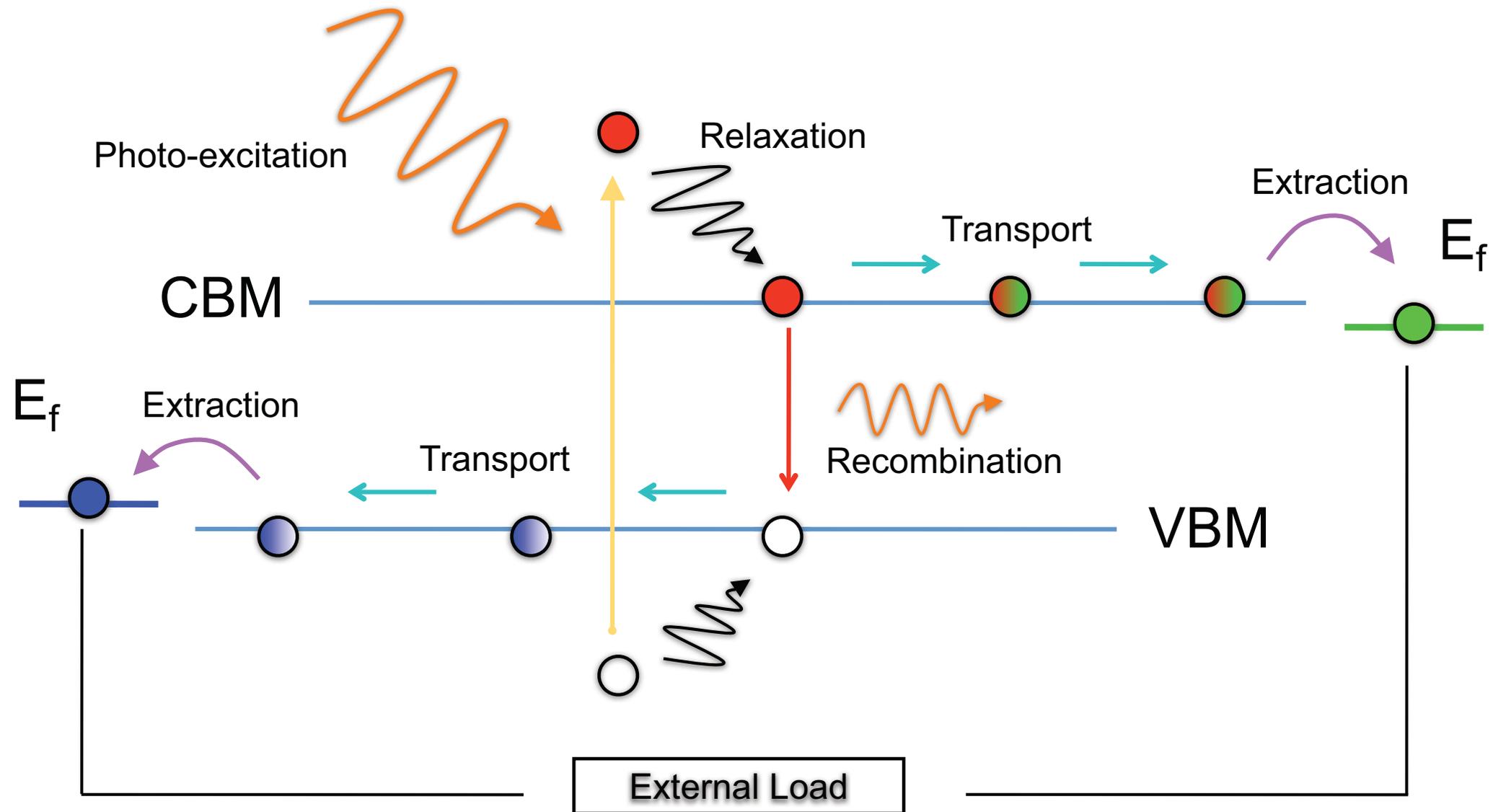
Comparison of PV Technologies

Best Research-Cell Efficiencies



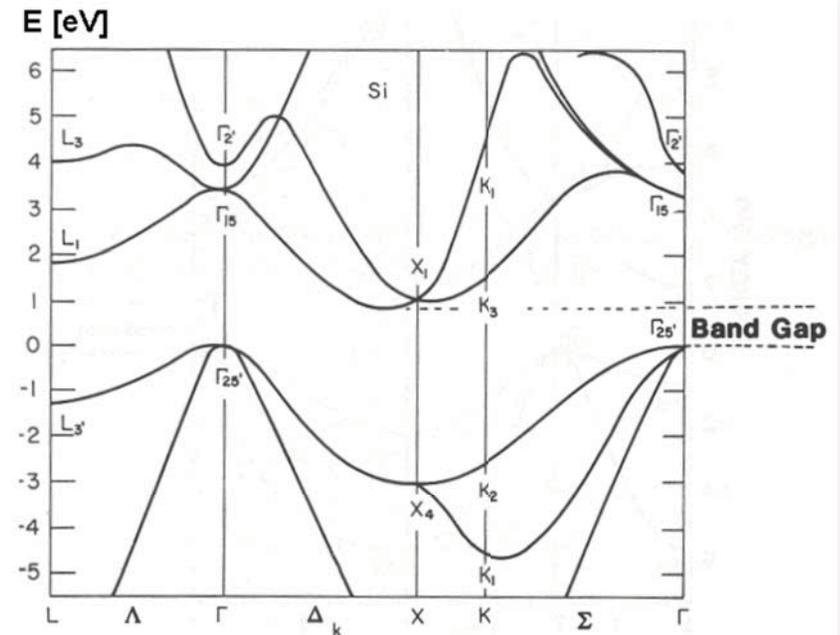
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Fundamental Processes Involved in Solar Photovoltaics: Electron's View



Crystalline Silicon Solar PV (80% of current market)

- Light Absorption
 - Band Gap
 - Band Structure



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- Electron/Hole Transport
 - Electron/Hole Mobilities

$$\sigma = e^2 \tau \int \frac{d\mathbf{k}}{4\pi^3} \left(-\frac{\partial f}{\partial E} \right) \mathbf{v}(\mathbf{k}) \mathbf{v}(\mathbf{k})$$

Amorphous Silicon Solar PV (3% of current market)

- Light Absorption (is actually pretty good)
- Electron-Hole Separation (also not a problem)
- Electron/Hole Transport (Holes are Slow!)
 - Hole Mobilities
 - Hole Traps: from total energy differences ($E_{\text{neutral}} - E_{\text{charged}}$)

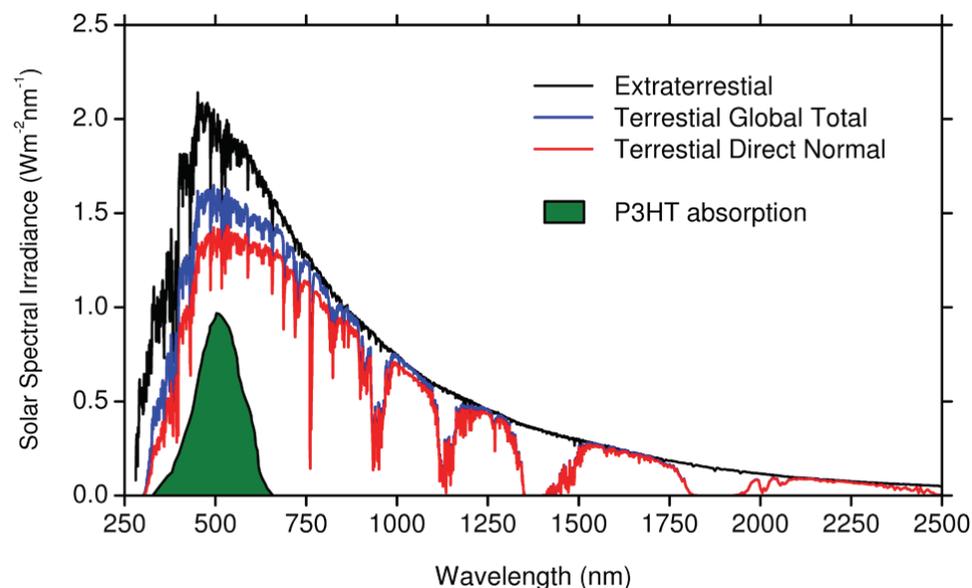
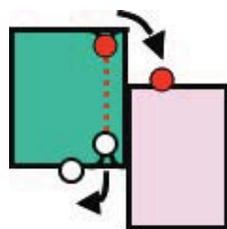
Organic Solar PV

- Light Absorption (need to capture more of the solar spectrum)

- Band gap

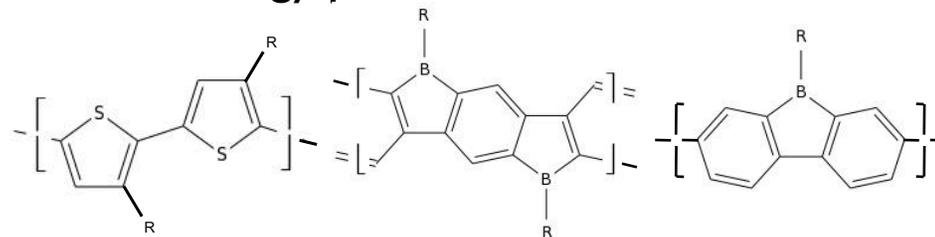
- Electron-Hole Separation

- Orbital energies



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Poly(3-hexylthiophene) (P3HT): $E_{g,exp} = 2.1$ eV
 Low-energy photons are not absorbed!



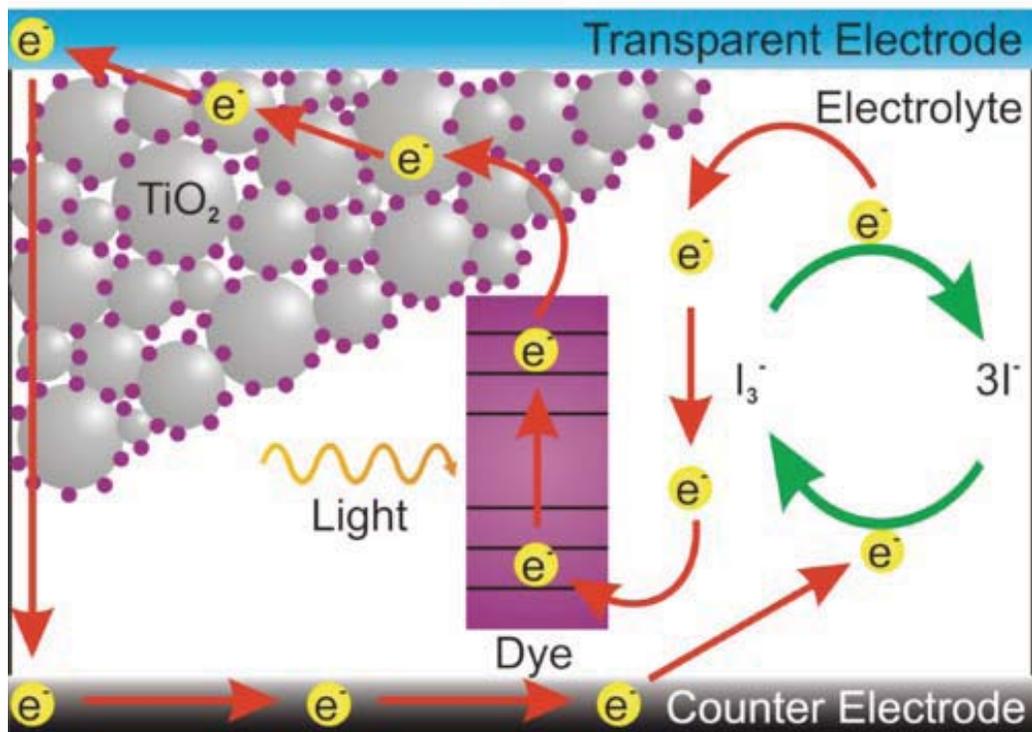
$$E_{gap} = E_0$$

$$E_{gap} = 0.55E_0$$

$$E_{gap} = 1.1E_0$$

Dye Sensitized Solar PV

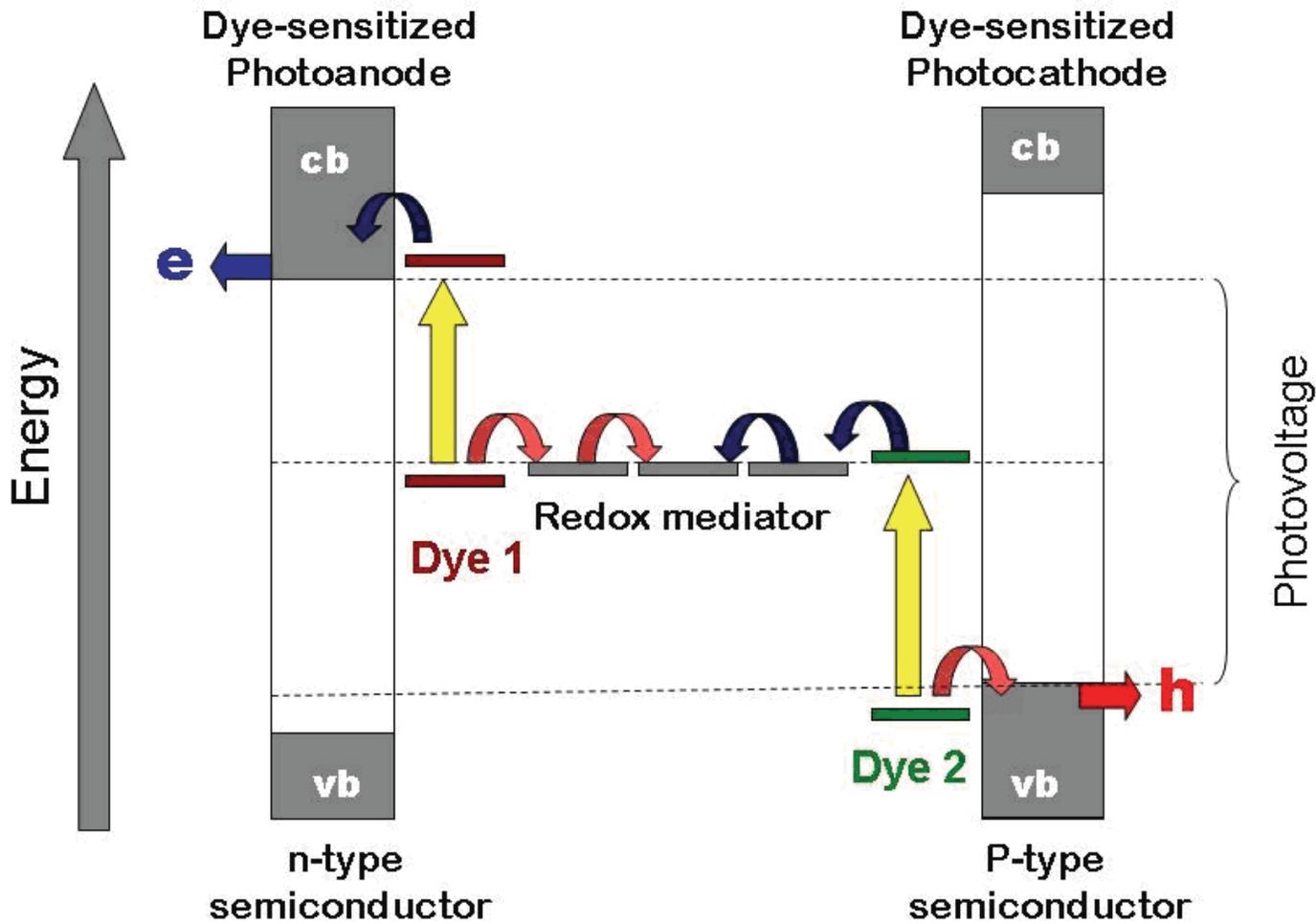
Gratzel and O'Regan
(Nature, 1991)



- Made up of 3 active materials:
- **Dye** absorbs light.
 - **TiO₂ nanoparticles** with very large surface area take electron.
 - Liquid **electrolyte** delivers new electron from cathode to dye.

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Dye Sensitized Solar PV



- Biggest problem is a liquid electrolyte.
- **Relative energy levels of TiO₂ and dye also key.**

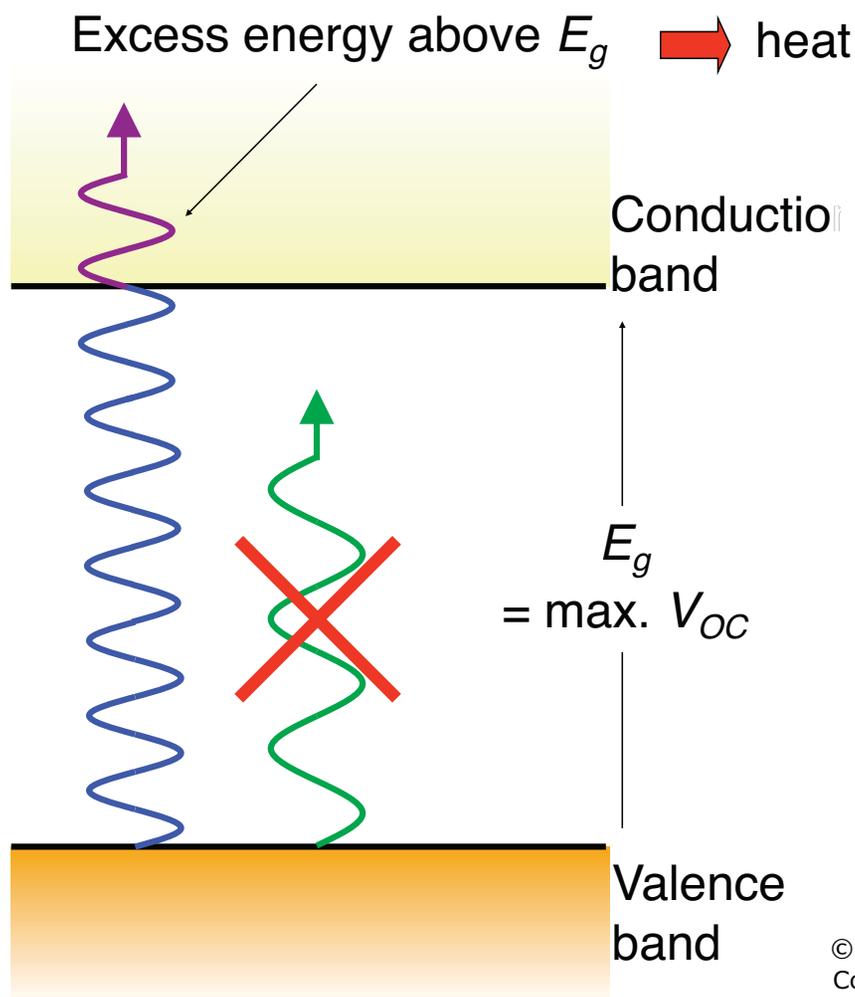
= electron transfer step

vb = valence band

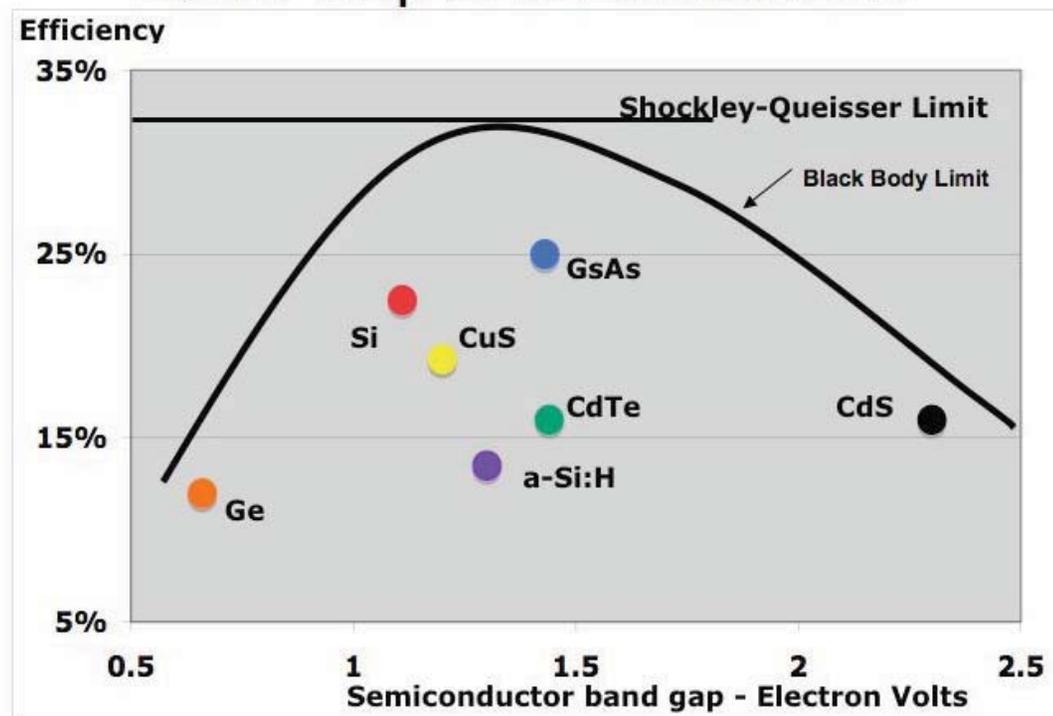
= hole transfer step

cb = conduction band

Going High Efficiency: Fundamental Limits



Band Gap and Efficiencies



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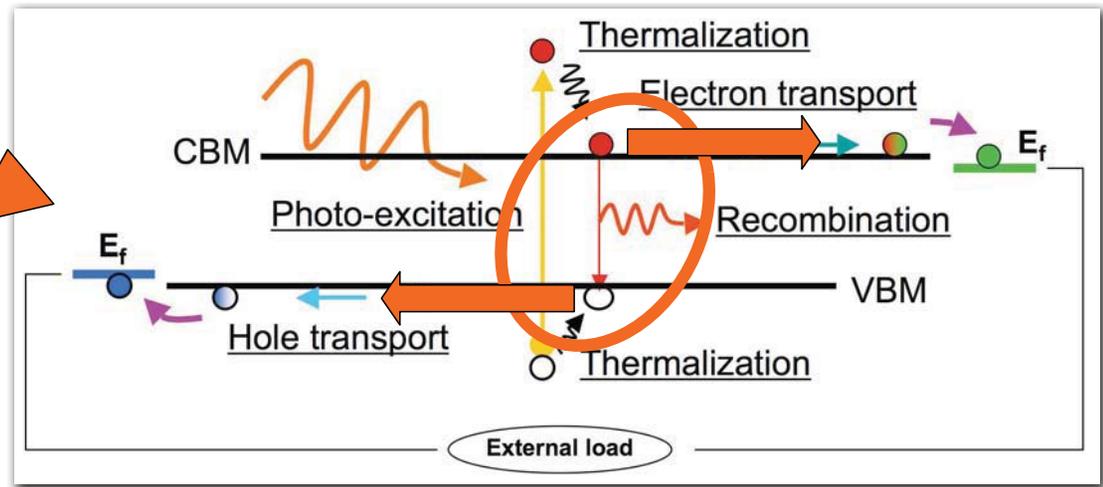
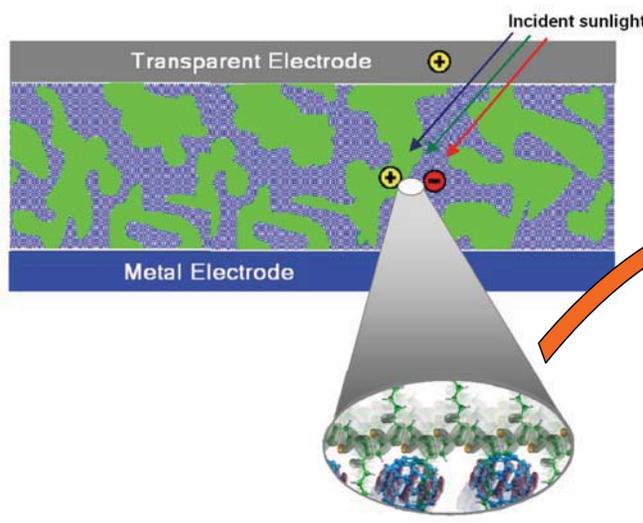
As band gap increases, the maximum open circuit voltage increases, but the fraction of the solar spectrum absorbed decreases.

Multi-Junction Solar PV

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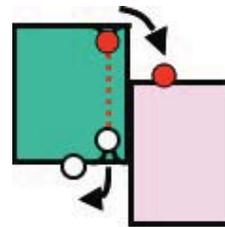
- Light Absorption
 - Band gaps
- Conductivity Across Interfaces
 - Band gaps, Band structures

Key Mechanism in Organic Solar PV: Charge Separation at the Interface



Charge separation at this interface is highly efficient*:

--Why?



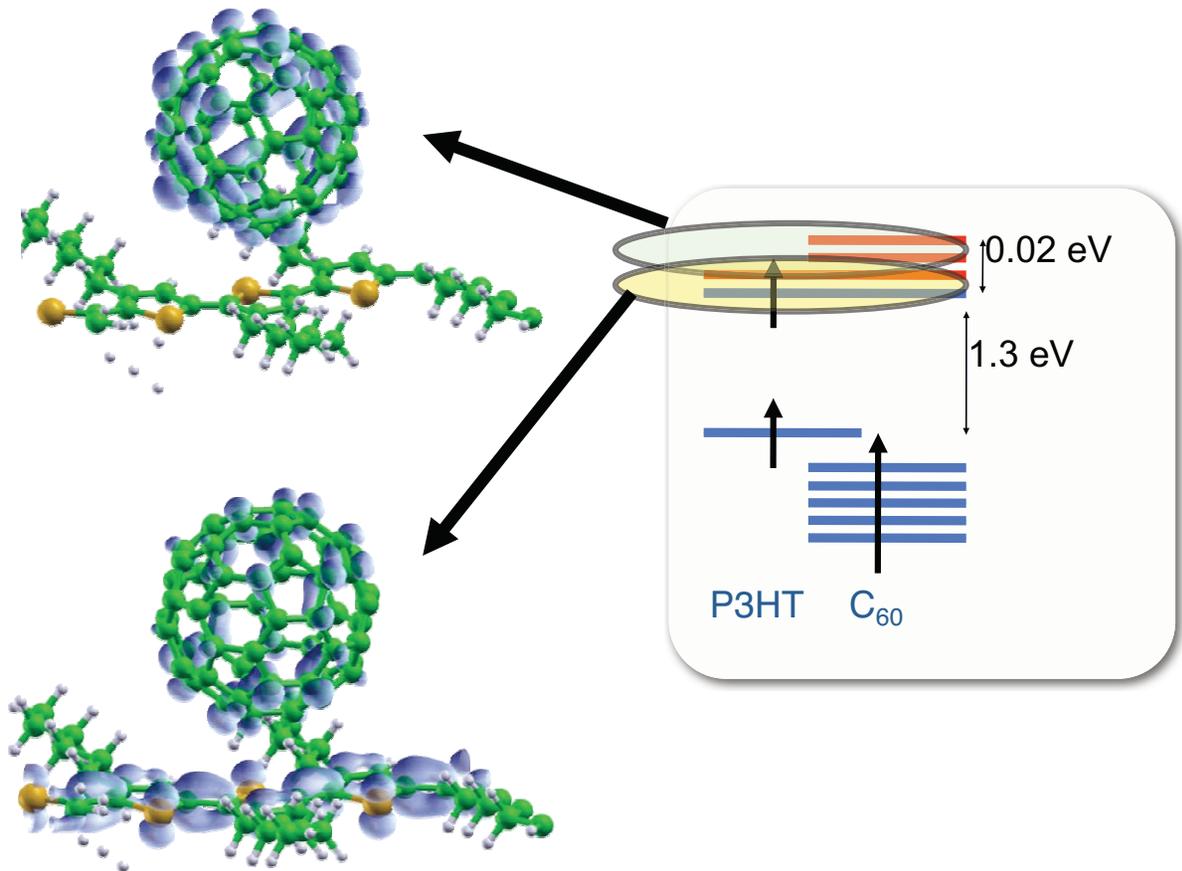
What is the detailed mechanism for this picture?

* N. S. Sariciftci et al., *Science*, 1992, 258, 1474
 B. Kraabel et al., *JCP*, 1996, 104, 4268
 C. J. Brabec. et al, *CPL*, 2001, 340, 232

Excited State

Charge separated state: essentially degenerate with bridge state.

Bridge state forms: hybridization of P3HT π^* state and C60 t_{1u} state.



CNT/P3HT: Metallic CNT

Carbon nanotubes instead of C60? Very little success thus far.*

E_f near P3HT
 π^* state

- Large charge transfer to the metallic CNT (~0.3 electron)
- Fermi level just above P3HT HOMO state
- No interface states are formed, so no E_f pinning
- Small built-in potential (0.06 eV), junction-induced exciton dissociation highly unlikely

Figures removed due to copyright restrictions. See Figures 4 and 5 in *Bano @etters* 8, no. 3 (2008).

CNT/Polymer solar cells unlikely to work well with mixed CNT distribution.

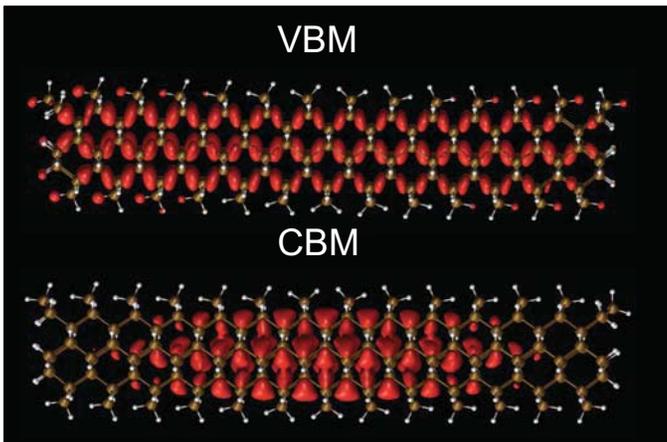


*e.g. Kymakis, E. et al. *Rev. Adv. Mater. Sci.* 2005, 10, 300

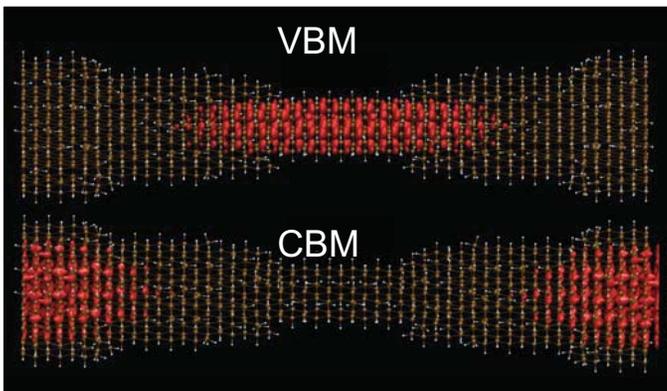
Y. Kanai and JCG, *NanoLett* (2008).

Using Computational Quantum Mechanics to Design **New** Mechanisms

Straight Wire

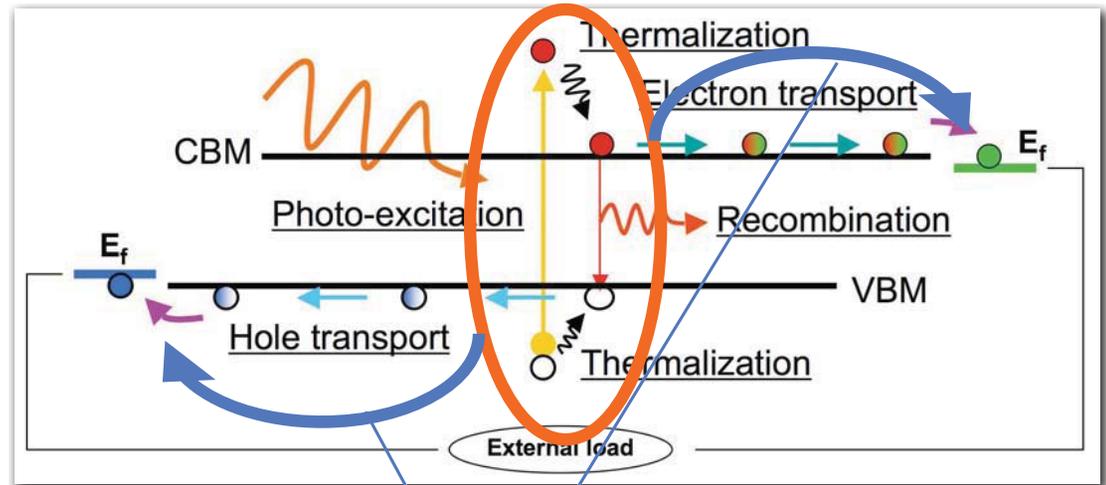


Tapered Wire

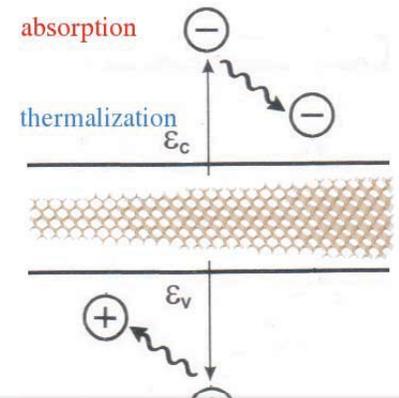


Axial charge redistribution due to quantum confinement

What could this mean for a solar cell?



Electron/hole charge separation through thermalization?



Major potential advantage: no doping needed!

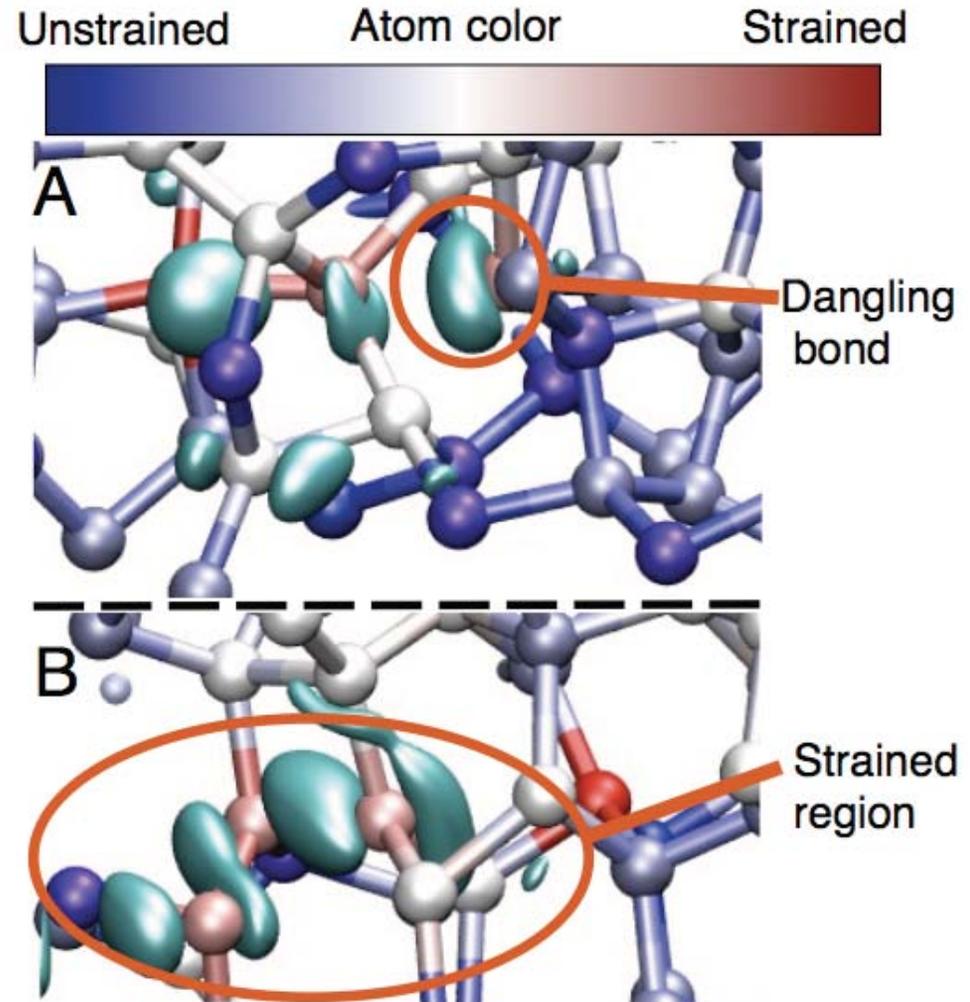


Hole Traps: Dangling Bond vs. Strain

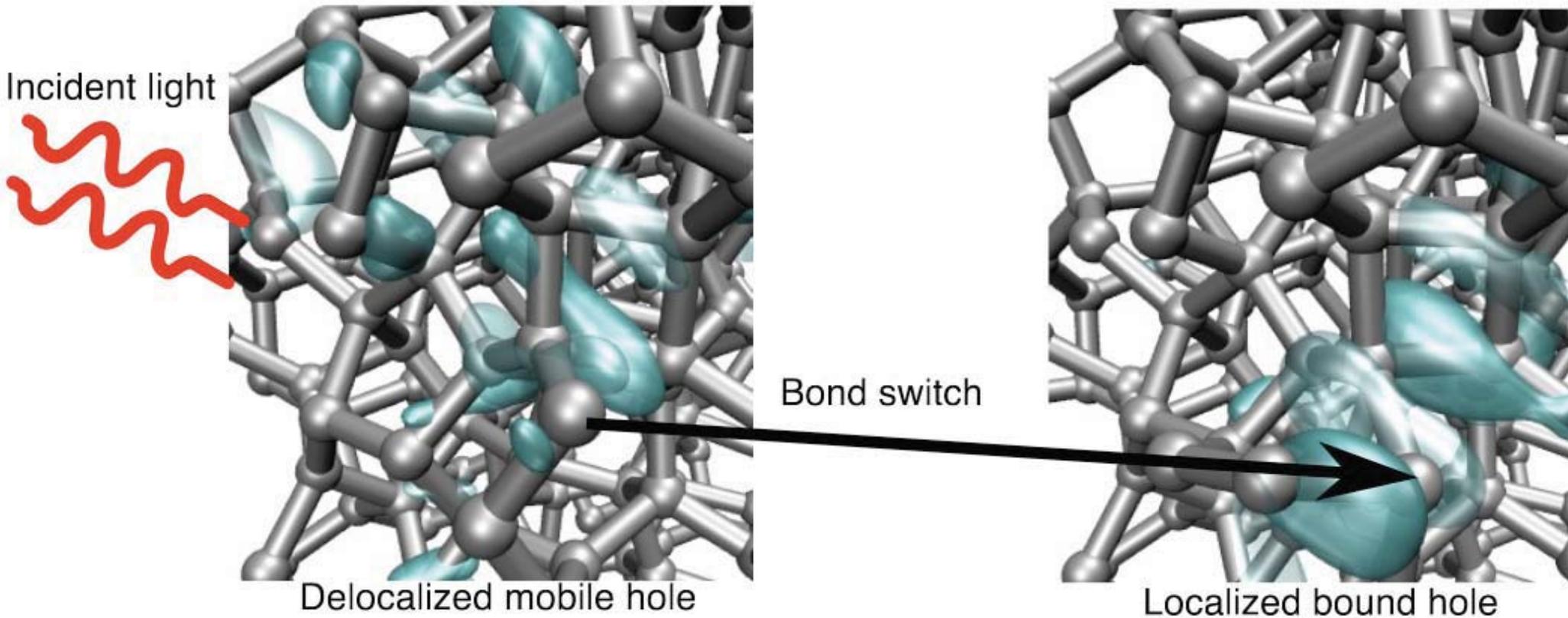
Dangling bond hole trap



Strain-only hole trap (stronger)



New Microscopic Picture of Holes in a-Si

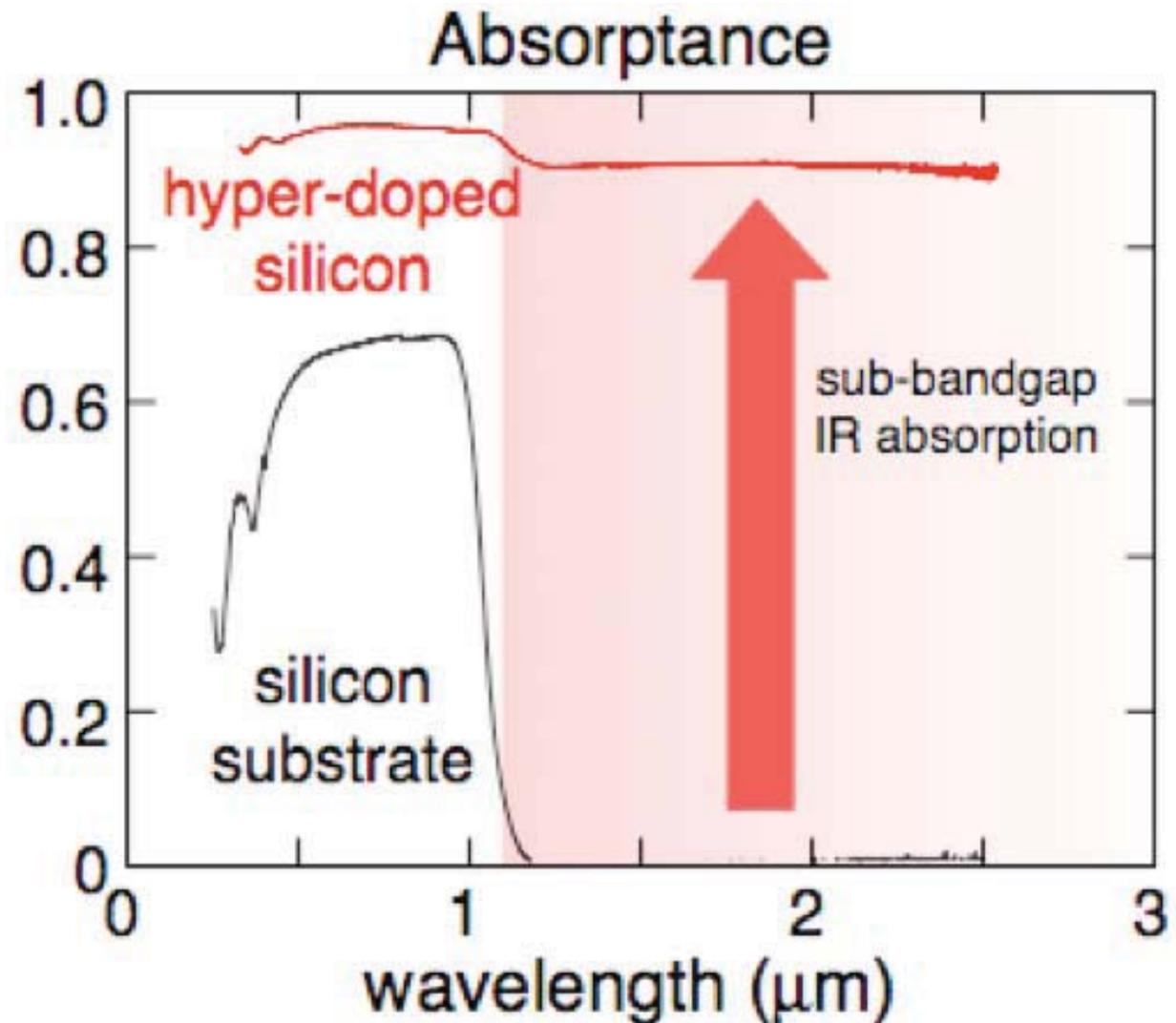


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Computational quantum mechanics shows that pressure can mitigate these traps!

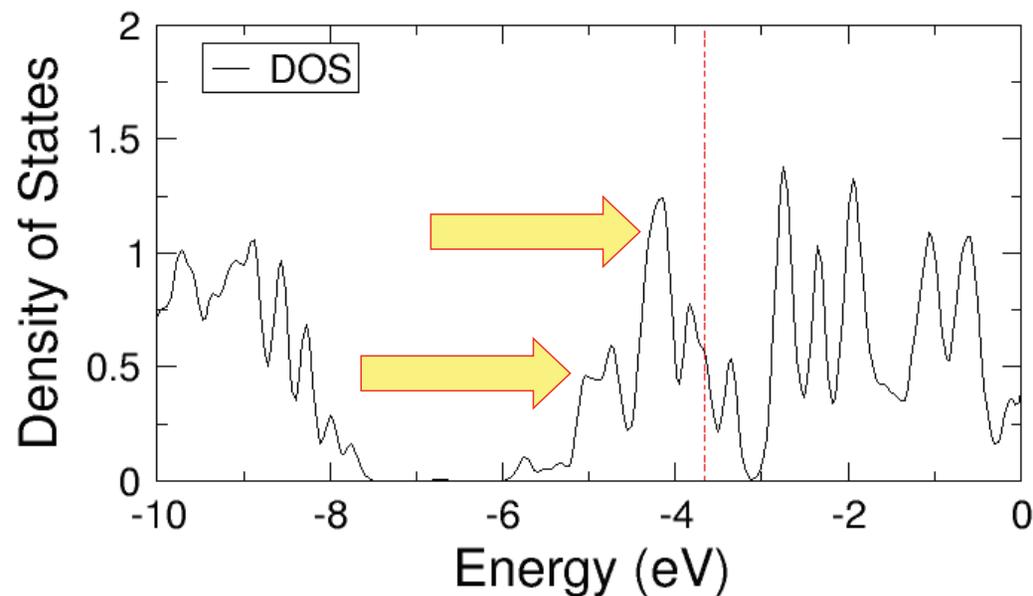
Another Thin-Film PV Example: Hyper-Doped Silicon

- Silicon doped with chalcogen atoms (sulfur, selenium, tellurium) to non-equilibrium concentrations.
- Strong optical response at photon energies where silicon is typically transparent.
- Promise as a photovoltaic material?

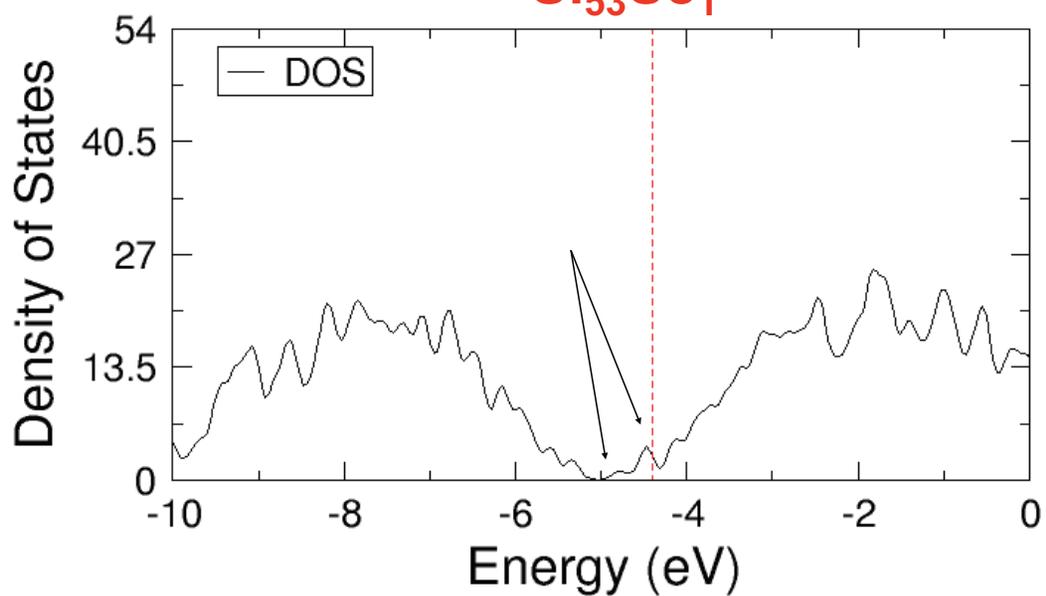


Evolution of Density of States

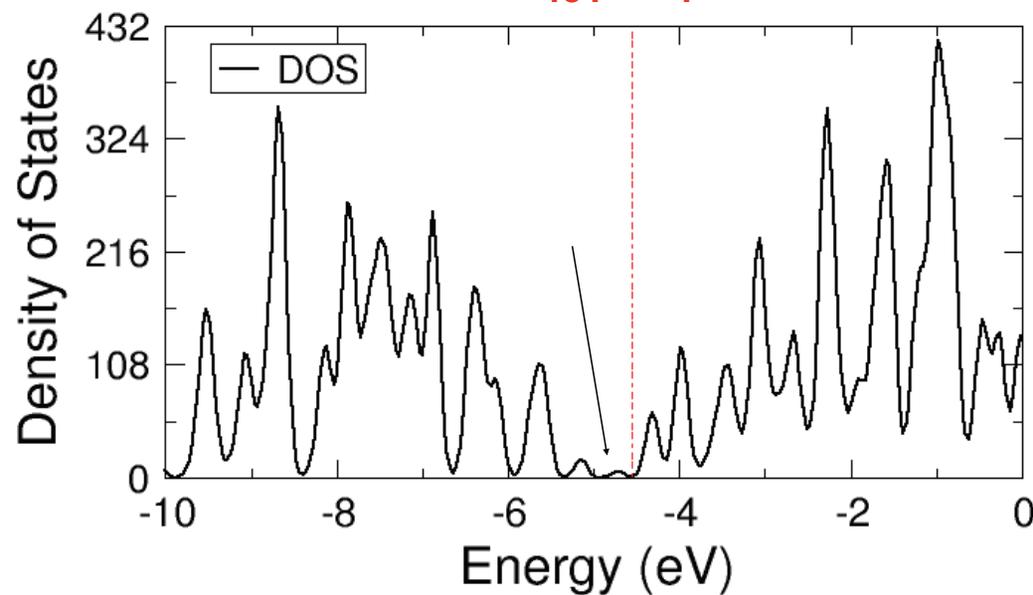
SiSe



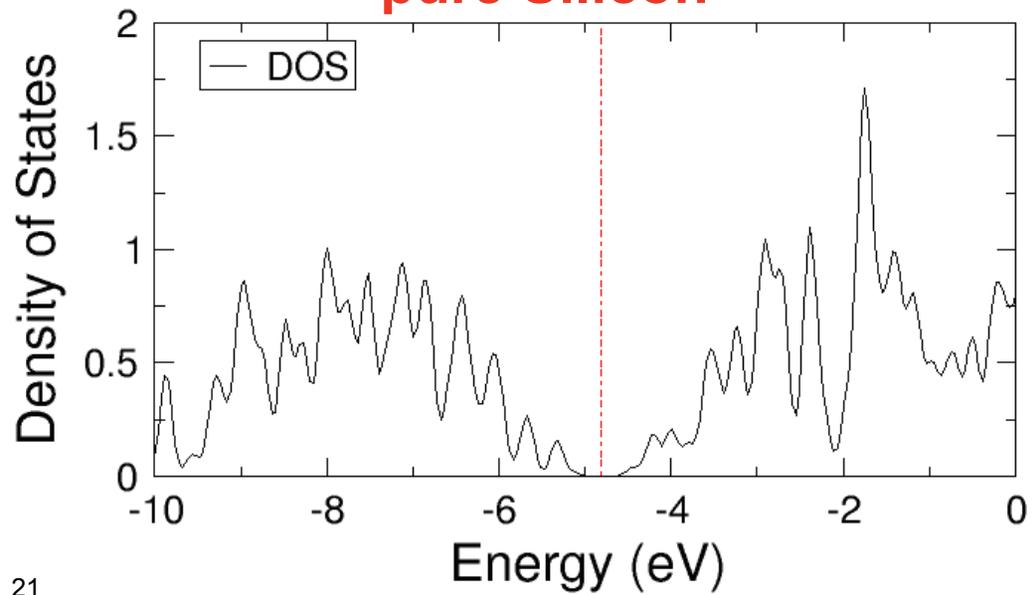
Si₅₃Se₁



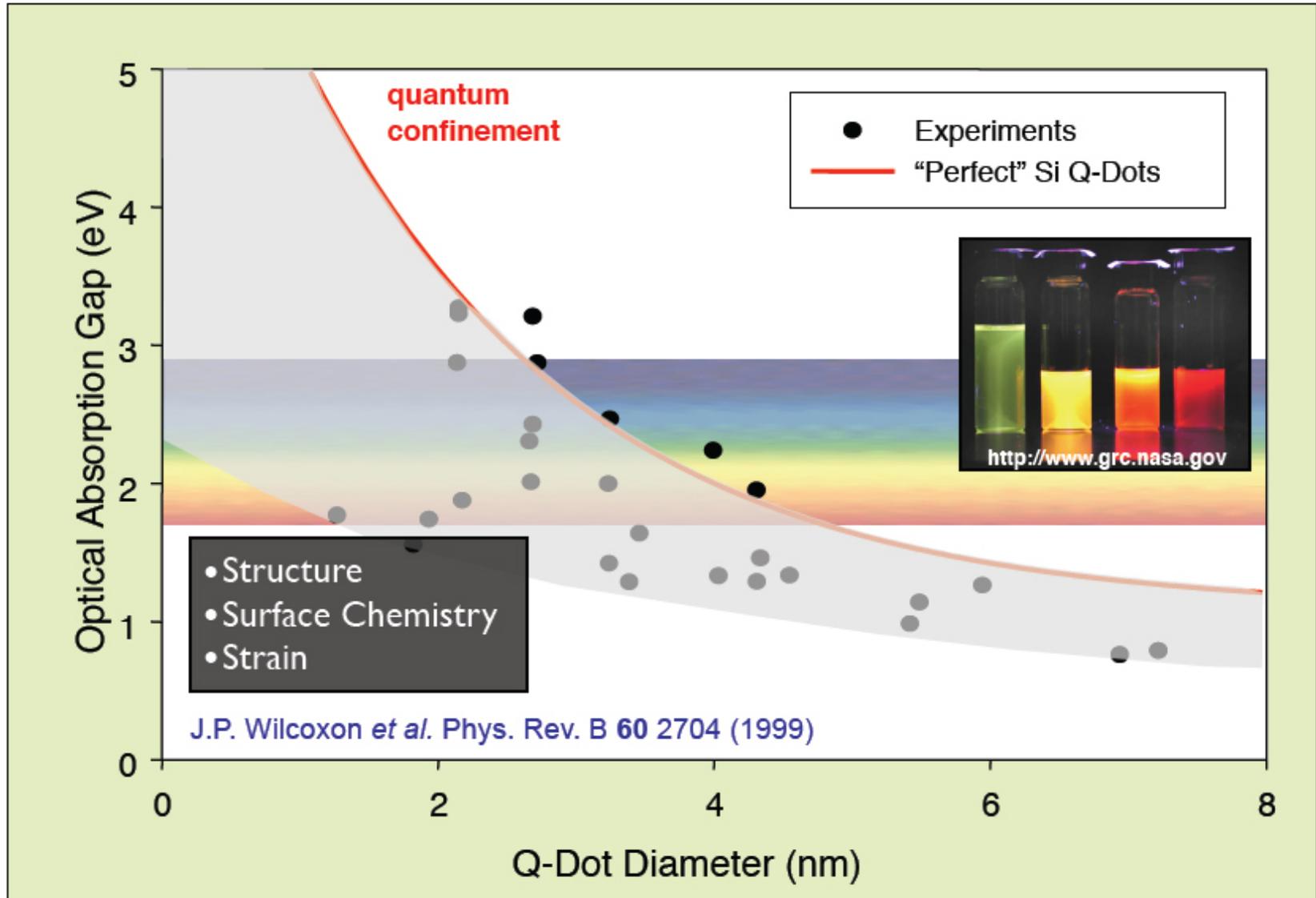
Si₄₃₁Se₁



pure Silicon

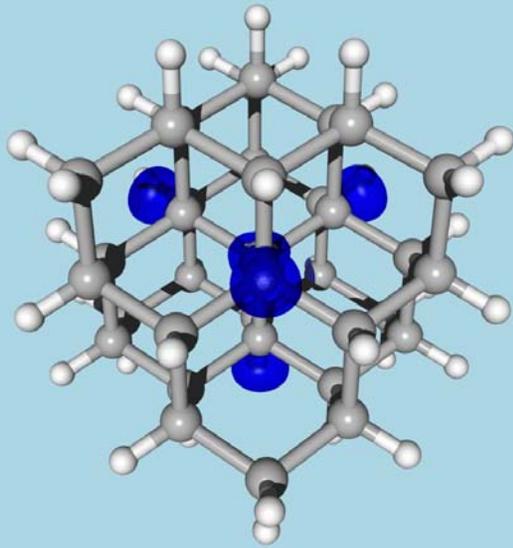


Needing to Know Structure and Chemistry



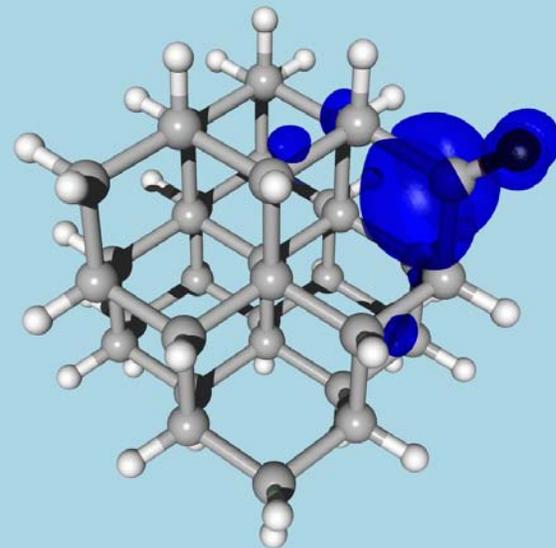
Needing to Know Structure and Chemistry

Clean Surface



Emits blue light

Oxygenated Cluster



Emits red light

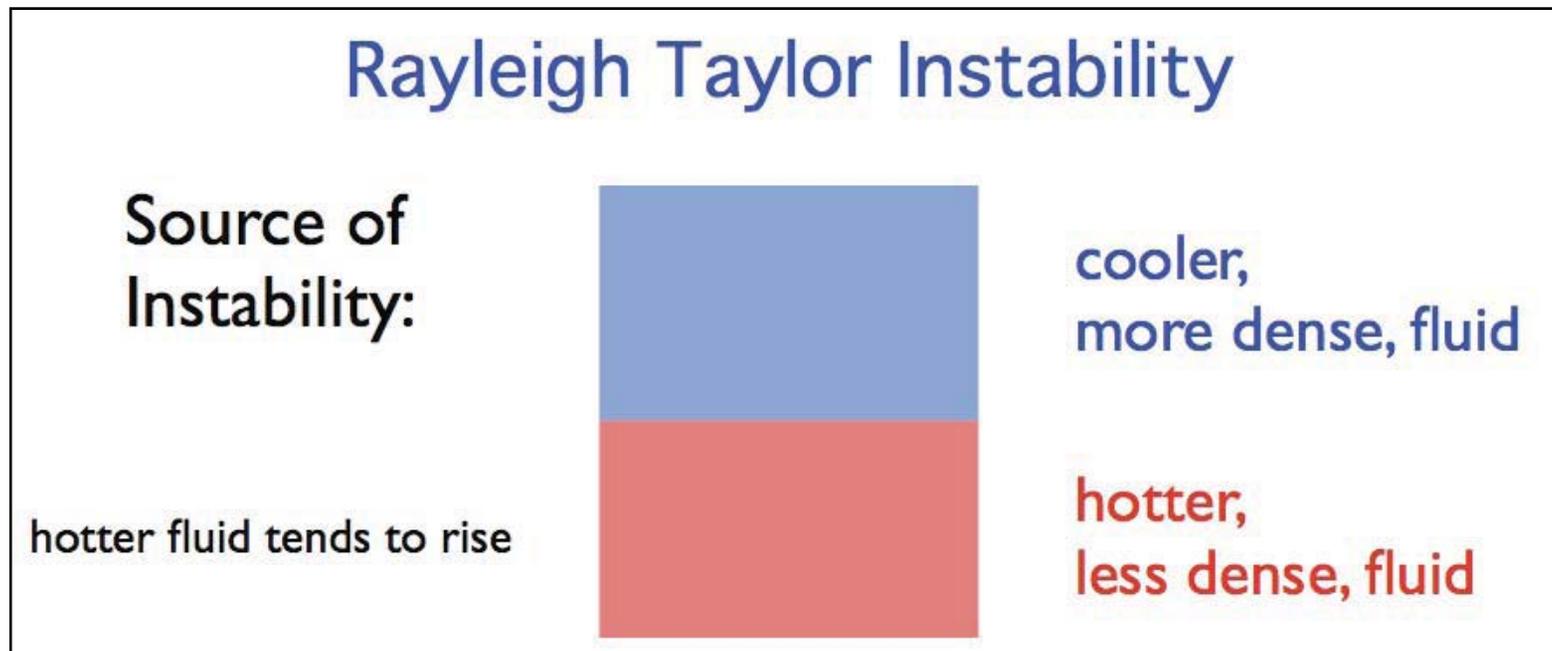
A. Puzder *et al.* Physical Review Letters, **88** 097401 (2002)

Validation

How do we know when a simulation is right?

Example: Rayleigh-Taylor Instability

From Leo P. Kadanoff, “The Good, the Bad, and the Awful
□ Scientific Simulation and Prediction”



Example: Rayleigh-Taylor Instability

- Idea: occurs anytime a dense, heavy fluid is accelerated into a light fluid or lesser density
- Slight perturbations to plane parallel interfaces are unstable ...fingers grow into sets of interpenetrating fingers
- Observed in weather inversions, salt domes, star nebulae
- How to model this process? Requires solving hydrodynamics equations.

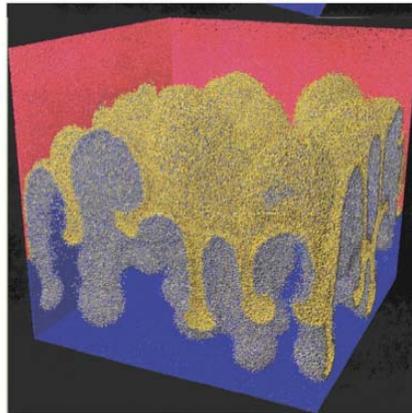
Example: Rayleigh-Taylor Instability

The Raleigh Taylor Instability.

Small deviations from perfect surface flatness triggers an instability. The two fluids penetrate into one another. Analysis (dimensional and RG arguments) suggest a penetration distance

$$h = \alpha A g t^2$$

with A being the Atwoods number (density contrast) and α being dimensionless---and also **Universal (!?)**.



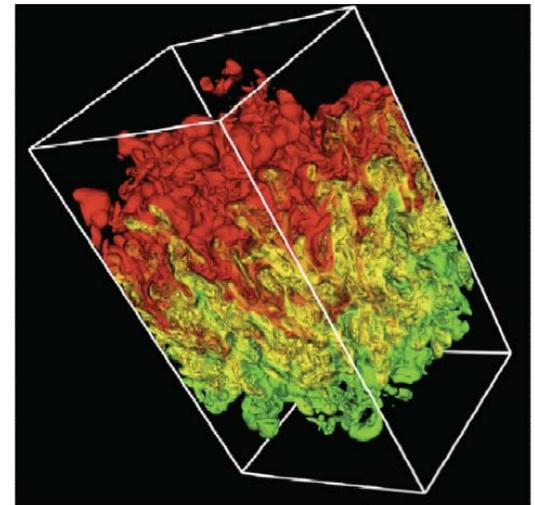
Kai Kadau...Berni Alder, "Nanohydrodynamics simulation of 10-5-07 R-T Instability", '04. $1.3 \cdot 10^8$ particles

Computer Simulations V2.9--For Berkeley

16

$$h = \alpha A g t^2$$

About 15 groups have measured or calculated α . Their results are important for us (a DOE supported astrophysics group) because the instability occurs on the surface of an exploding star.



Fluid Mechanics Simulation of RT instability. "On Validating an Astrophysical Simulation Code". A. C. Calder, et al. *Astrophys.J.Supp.* **143** 201-230 (2002). The value of α differs from previous picture by a factor of two.

Computer Simulations V2.9--For Berkeley

10-5-07

17

Example: Rayleigh-Taylor Instability

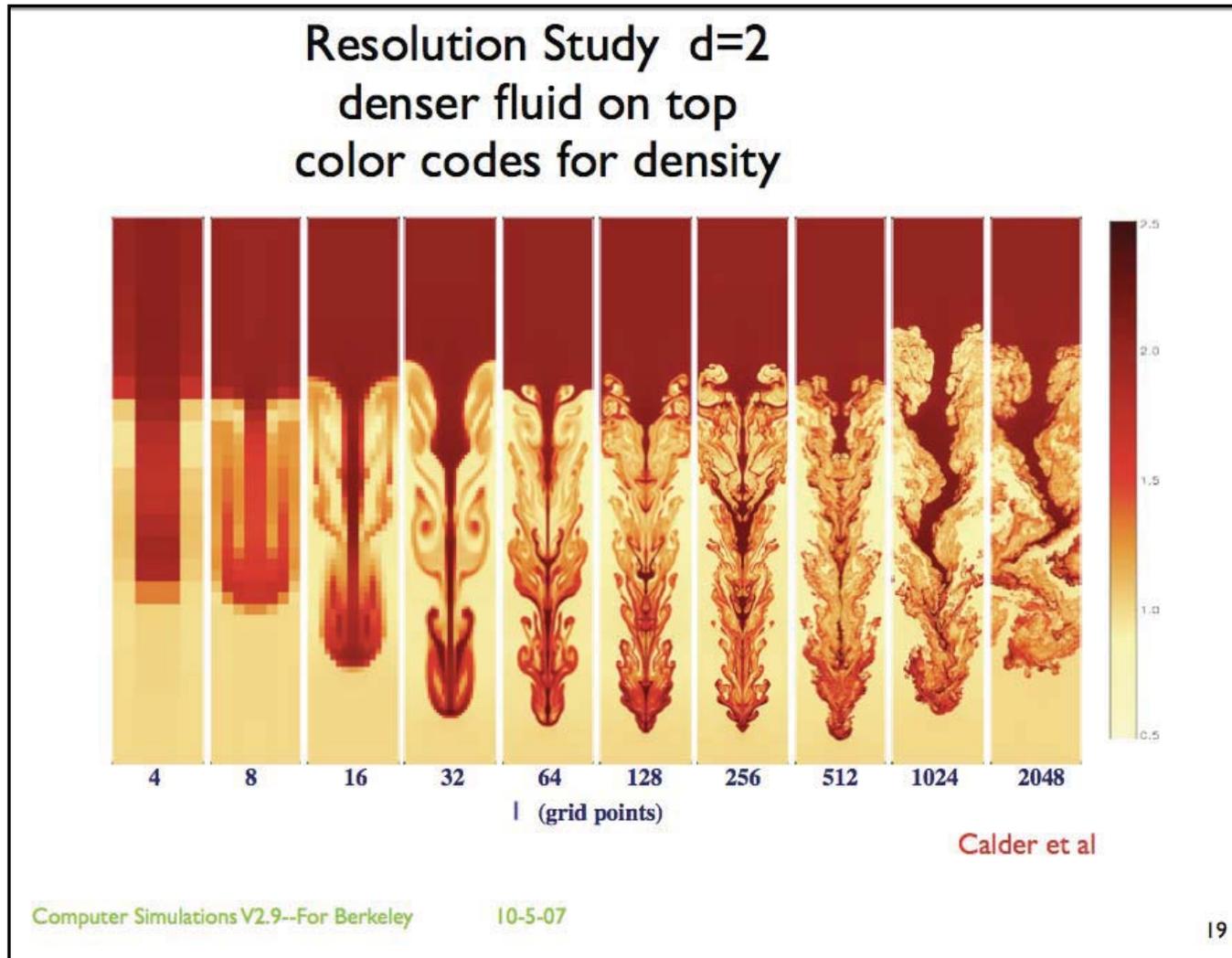


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Validation and Verification

Verification and validation (V&V) are processes that help to ensure that models and simulations are correct and reliable.

Verification: “Did I build the thing right?”

Have the model and simulation been built so that they fully satisfy the developer’s intent?

Validation: “Did I build the right thing?”

Will the model or simulation be able to adequately support its intended use? Is its fidelity appropriate for that?

We've learned a lot!

Some of the key remaining challenges

The electron correlation problem. *Only seriously affects a fraction of materials, but that fraction tends to contain interesting physics and technological potential. At this point there is no logical follow-up on LDA/GGA*

Some of the key remaining challenges

The time-scale problem. *Short (MD) and long (thermo) is not a problem. Intermediate is a problem. e.g. phase transformations.*

Some of the key remaining challenges

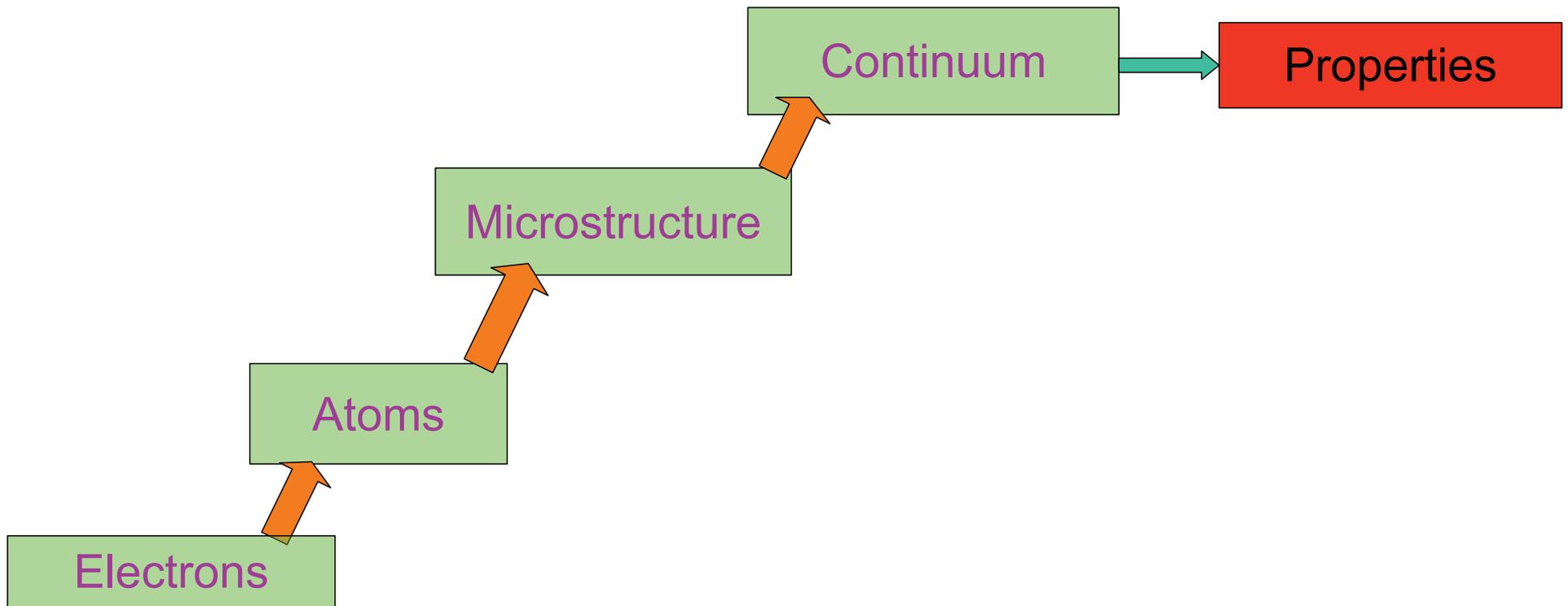
The knowledge problem. *To study an engineering property/behavior with atomistic-scale modeling, one needs to understand somewhat what controls that property (in order to include the relevant boundary conditions).*

e.g. If a property is controlled by impurities then intrinsic calculations will be irrelevant (Si conductivity).

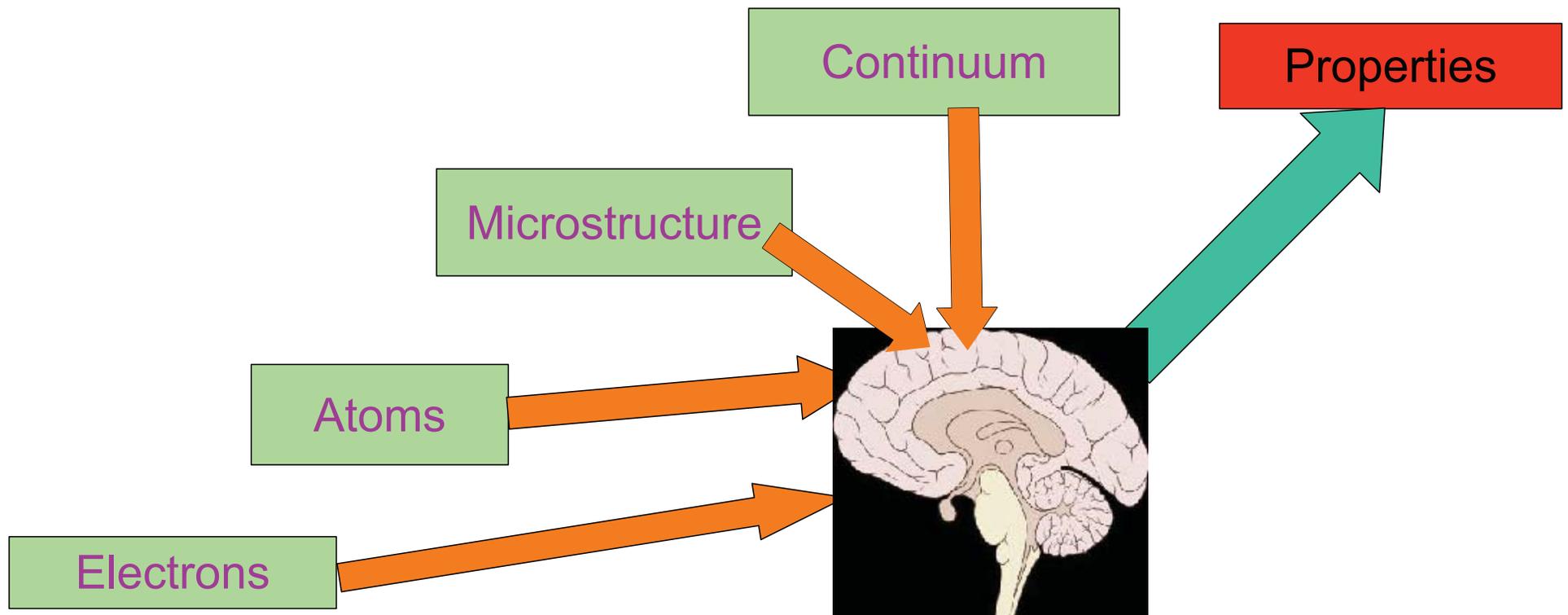
Some of the key remaining challenges

The structure problem. *Even though the structure-property relation is a key tenet of Materials Science, we have only very limited ability to predict structure (crystal structure, amorphous, microstructure, ...)*

Theory of Properties: The Multi-Scale Materials View



Theory of Properties: The Multi-Scale Materials View



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**Computations should not
substitute for lack of
knowledge**

Computational modeling is very
powerful, but **be smart!**

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Spring 2012

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